

Conference Organization

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Fabrizio Roccaforte (CNR-IMM, Italy)

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David Pulfrey, U. British Columbia, Canada

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Local Scientific Committee

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Filippo Giannazzo

Raffaella Lo Nigro

Vito Raineri

Fabrizio Roccaforte

Local Organizing Committee

Salvatore Di Franco

Francesca Nizza

Nicolò Parasole

Aldo Spada

Venue

The conference will be held in Catania, the second city of Sicily, which is situated on the east coast of the Island. The international airport offers daily connections with the major national destinations and with several European cities.

Many tourist places can be easily reached from Catania, such as the mount Etna (the highest active volcano in Europe), Taormina, Piazza Armerina, Syracuse.

The scientific sessions will be held in the Pinacoteca of the Diocesan Museum of Catania, situated in the ancient Seminario dei Chierici of the Chatedral, in the heart of the old town.

Social Events

A trip to Taormina will be organized on Tuesday, May 31st afternoon, which will be followed by the social dinner. Furthermore, an excursion to mount Etna is foreseen on June 2nd.

Contacts

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35th Workshop on Compound Semiconductor Devices and Integrated Circuits

Catania (Italy)
29th May – 1st June, 2011



Consiglio Nazionale delle Ricerche
Istituto per la Microelettronica e Microsistemi

Scope

The aim of the 35th Workshop on Compound Semiconductor Devices and Integrated Circuits is to bring together internationally recognised researchers, young scientists and engineers to present state-of-the-art research findings in the areas of compound semiconductors, devices and integrated circuits. In these fields, an intense activity is currently carried out in Catania, thanks to the cooperation between the Institute for Microelectronics and Microsystems of the National Council for Research, the University, and several industries and private research centres, together forming the “Etna Valley”. Hence, the workshop welcomes both researchers from universities and research institutions, and scientists and engineers working in industry.

Traditionally, with participants from almost 20 countries, WOCSDICE has been a forum for regular European meetings bringing together the leading experts from all over the world.

It is the wish of the organizers to maintain a tradition of intensive and informal scientific discussions and interactions between young researchers and experts in the field.

A special emphasis will be given to III-V compounds and large-area scaling; III-nitride materials, devices, for both optoelectronics and power electronics, and related reliability aspects; high-frequency circuits and optical interconnects. The focus will be extended towards advanced devices on organic semiconductors and novel materials like graphene.

You are invited to submit a paper for oral presentation in one of the conference topics. However, suggestions of any other topic in which you are expert and would like to present within the scope of the conference are welcome.

Topics

Epitaxy, material aspects and characterization

GaN on Si
III-nitrides and SiC heterostructures
Graphene and carbon nanostructures
Substrates: Bulk crystals, SOI, SiC and diamond
Wafer-bonding and transferred-substrate techniques
Methodology, simulations

Processing, Reliability and Packaging

Surface passivation, etching, nanolithography
High-k dielectrics
Packaging solutions
Wide bandgap devices and MMICs reliability
Thermal degradation

Optoelectronics and Optics

Optical switching, networking and signal processing
Waveguides, Photonic crystals
Integration opto-microelectronic
DUV, EUV, X-ray photonics applications

Electron Devices and Circuits

MW and mm-waves Integrated Circuits
Low Noise device and circuit performance
Terahertz technology (THz imaging)
Plasmonics
Novel devices, novel structures and concepts
Wide bandgap devices
High Voltage Switching devices
High power – High frequency devices
Graphene electronics, quantum structures
Microsystems, MEMS, NEMS, MOEMS
Organic Devices: FET, LED, LD, VCSELs
Detectors

Advanced photovoltaics

III-V and II-VI solar cells
PV 3rd generation
Organic PV & Storage
Sensors, biosensor, energy harvesters including novel solar cells

Important Dates

Final announcement and call for abstracts:
January 2011

Short-abstract submission deadline:
February 25, 2011

Notification of acceptance:
March 21, 2011

Early registration deadline (reduced fee):
April 4, 2011

Extended-abstract submission deadline:
April 11, 2011

Notes for authors

The official language of the conference is English, which will be used for all presentations and printed materials. Authors are expected to present their papers in person at the conference.

Conference proceedings

The authors of accepted works will be asked to submit an extended abstract (2 pages) at least one month in advance of the conference. The manuscript format and detailed instructions will be found in the conference web-page.

An extended abstract book will be printed and distributed to all the participants during the conference. The electronic version will be published on-line.